DOCKET NO. 108430.025D Scrial No. 10/634,330 Response to Office Action dated Feb. 17, 2004

**PATENT** 

## Amendments to the Claims

This listing will replace all prior versions, and listings, of claims in the application:

Claim 1 (Currently Amended): A process for removing photoresist from semiconductor wafers comprising:

positioning at least one semiconductor wafer in a process tank; and

- (a) mixing introducing a mixture of said ozone with and deionized water to the process tank via a sparger plate at an increased flow velocity across said wafer while said wafer is submerged in said deionized water and ozone.; and
- (b) exposing semiconductor wafers having at least one layer of photoresist to said mixture of ozone and deionized water.

Claim 2 (Cancelled).

Claim 3 (Currently Amended): The process according to claim 1 further comprising the maintaining the temperature in the processing tank at ambient temperature.

Claim 4 (Original): The process according to claim 3 wherein the temperature is about 20-21 °C.

Claim 5 (Original): The process according to claim 3 wherein the temperature is above 20-21 ° C.

Claim 6 (Original): The process according to claim 1 wherein the mixture of ozone and deionized water is recirculated and flows back into the processing tank.

Claim 7 (Original): The process according to claim 1 wherein the mixture of deionized water and ozone is recirculated and ozone added so as to keep the concentration of ozone in said mixture about constant.

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Claim 8 (Original): The process according to claim 7 wherein said mixture of deionized water and ozone is agitated via the sparger plate.